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IN THE SPECIFICATION

Page 11, replace the first paragraph with the following replacement paragraph:

--In the present embodiment, the characteristics of the ITO film 2 are set such that the work function is 4.9 to 5.5 eV, the surface roughness is 1 to 10 nm, and the specific resistance is 1.0×10^{-4} to $1.6 \times 10^{-4} \Omega \cdot \text{cm}$. Further, the ITO film 2 set as above can be formed easily on the surface of the glass substrate 1 by an ion plating method by using a sintered compact of ITO set to have an SnO_2 content of 4 to 6 wt% as a film-forming tablet (material to be vaporized).--